AMENDMENTS TO THE CLAIMS

The following listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device comprising:

a semiconductor element;

a first metal plate bonded to one side of the semiconductor element;

an intermediate layer bonded to one side of the first metal plate remote from the semiconductor element, the intermediate layer being made of a carbon-copper composite material;

a second metal plate bonded to one side of the intermediate layer remote from the first metal plate;

an insulating member bonded to one side of the second metal plate remote from the intermediate layer; and

a third metal plate bonded to one side of the insulating member remote from the second metal plate, the third metal plate having a thickness substantially equal to that of the second metal plate; and,

a heat sink;~~ and~~

wherein the first, second and third metal plates are made of a same material~~an intermediate layer provided between the semiconductor element and the heat sink to moderate thermal stress~~.

2. (Currently Amended) ~~A~~ The semiconductor device according to claim 1, wherein the intermediate layer ~~for moderating~~ is adapted to moderate thermal stress ~~comprises a carbon-copper composite material~~.

3. (Original) A semiconductor device comprising:

a semiconductor element;

a heat sink;

a laminar plate provided between the semiconductor element and the heat sink, said laminar plate including ~~so as to include~~ an intermediate layer for moderating thermal stress.

4. (Currently Amended) ~~A~~ The semiconductor device according to claim 3, wherein the laminar plate comprises a first metal plate, the intermediate layer, a second metal plate, an insulating member, and a third metal plate, wherein:

said ~~a~~ first metal plate being interposed between the ~~bonded to~~ the semiconductor element and the intermediate layer, said first metal plate having one side bonded to the semiconductor element and an opposite side bonded to a first side of the intermediate layer;

~~the intermediate layer for moderating thermal stress, bonded to the opposite side of the first metal plate from the semiconductor element;~~

said ~~a~~ second metal plate being interposed between the intermediate layer and the insulating member, whereby one side of said second metal plate is bonded to a second, opposite side of the intermediate layer and the other side of said

second metal plate is bonded to ~~the opposite side of the intermediate layer from the side thereof bonded to the first metal plate;~~

~~an insulating member bonded to the opposite side of the second metal plate to the side thereof bonded to~~ a first side of the intermediate layer; and

~~a~~ said insulating member is interposed between the second and third metal plates, whereby said third metal plate is bonded to ~~the~~ a second, opposite side of the insulating member~~to the side thereof bonded to the second metal plate~~.

5. (Currently Amended) ~~A~~ The semiconductor device according to claim 4, wherein ~~the~~ a thickness of the second metal plate is equal to a ~~and the~~ thickness of the third metal plate ~~are equal~~.

6. (Currently Amended) ~~A~~ The semiconductor device according to claim 3, wherein the intermediate layer for moderating thermal stress comprises a carbon-copper composite material.